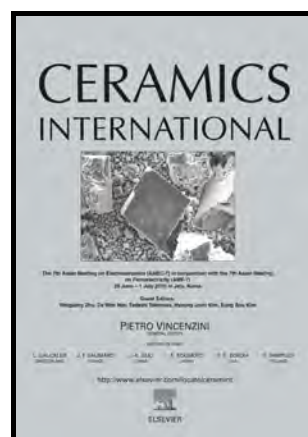


Crystal structure, microwave dielectric properties and low temperature sintering of  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  co-substitution for  $\text{Ti}^{4+}$  of  $\text{LiNb}_{0.6}\text{Ti}_{0.5}\text{O}_3$  ceramics

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# Crystal structure, microwave dielectric properties and low temperature sintering of $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$ co-substitution for $\text{Ti}^{4+}$ of $\text{LiNb}_{0.6}\text{Ti}_{0.5}\text{O}_3$ ceramics

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## Abstract

The phase composition, microstructure, microwave dielectric properties of  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  co-substitution for Ti site in  $\text{LiNb}_{0.6}\text{Ti}_{0.5}\text{O}_3$  ceramics and the low temperature sintering behaviors of  $\text{Li}_2\text{O-B}_2\text{O}_3\text{-SiO}_2$  (LBS) glass were systematically discussed. XRD patterns and EDS analysis result confirmed that single phase of  $\text{Li}_{1.075}\text{Nb}_{0.625}\text{Ti}_{0.45}\text{O}_3$  solid solution was formed in all component. The increase of dielectric constant ( $\epsilon_r$ ) is ascribed to the improvement of bulk density. The restricted growth of grain has a negative influence on quality factor ( $Q \times f$ ) value. The  $\tau_f$  value could be continuously shifted to near zero as the doping content increases. Great microwave dielectric properties were obtained in  $\text{LiNb}_{0.6}\text{Ti}_{(0.5-x)}(\text{Al}_{0.5}\text{Nb}_{0.5})_x\text{O}_3$  ceramics ( $x = 0.10$ ) when sintered at  $1100^\circ\text{C}$  for 2 h:  $\epsilon_r = 70.34$ ,  $Q \times f = 5144$  GHz,  $\tau_f = 4.8\text{ppm}/^\circ\text{C}$ . The sintering aid, LBS glass, can effectively reduce the temperature and remain satisfied microwave performance. Excellent microwave dielectric properties for  $x = 0.10$  were obtained with 1.0 wt. % glass:  $\epsilon_r = 70.16$ ,  $Q \times f = 4153$  GHz (at 4

GHz),  $\tau_f = -0.65 \text{ ppm}/^\circ\text{C}$  when sintered at  $925^\circ\text{C}$  for 2 h.

**Keywords:**  $\text{LiNb}_{0.6}\text{Ti}_{0.5}\text{O}_3$  ceramics, microwave dielectric properties,  $\text{Li}_2\text{O-B}_2\text{O}_3\text{-SiO}_2$  (LBS) glass, low temperature sintering.

## 1 Introduction

Due to the fast growth of the modern telecommunications devices, lead-free high performance microwave dielectric ceramics with an appropriate property were widely used [1-4]. Three key properties need to be balanced for these ceramics: a large dielectric permittivity ( $\epsilon_r$ ), high quality factor ( $Q \times f$ , where  $f$  stands for the resonant frequency) and a near zero temperature coefficient of resonant frequency ( $\tau_f$ ). In addition, a low sintering temperature is necessary for Low Temperature Co-fired Ceramic (LTCC) [5-7].

Recently, a series novel Li-based  $\text{Li}_2\text{O-Nb}_2\text{O}_5\text{-TiO}_2$  system dielectric material were studied systematically owing to its excellent performance.  $\text{Li}_{1+x-y}\text{Nb}_{1-x-3y}\text{Ti}_{x+4y}\text{O}_3$  (M phase) solid solutions was firstly reported by Villafuerte-Castrejon in 1987[8]. On the basis of their research, HRTEM and single-crystal X-ray diffraction was utilized by L. Farber[9] to investigate the structure of M phase, and they illustrated that the solid solutions were consisted of  $n$  layers of  $\text{LiNbO}_3$ -type slabs, and a layer of a corundum-type structure ( $\text{Ti}_2\text{O}_3^{2+}$ ) was inserted in the propagating chains of  $\text{LiNbO}_3$ -like chains, and  $n$  is dependent on the content of Ti. Albina Y. Borisevich[10] introduced the microwave characterization of M phase. And then, for the purpose of improving the dielectric characterization of M phase, lots of researchers have made many attempts. For instance, the  $\epsilon_r$  will increase and  $\tau_f$  can be adjusted to near zero while a small number of  $\text{Ca}^{2+}$  substitutes for  $\text{Ti}^{4+}$ . Due to the inevitable volatilization of Li element during high temperature sintering, excessive Li was used, which enhanced the microwave characterization subsequently[11, 12].

The  $\tau_f$  value reflects stability of ceramics, and a near zero  $\tau_f$  value means that the ceramics can work stably in a temperature range[13]. To adjust the  $\tau_f$  value of  $\text{LiNb}_{0.6}\text{Ti}_{0.5}\text{O}_3$  ( $30.6 \text{ ppm}/^\circ\text{C}$ ), a solid solution was designed, after referring the radius of  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  ( $\text{IR}=0.588\text{\AA}$  CN=6) and  $\text{Ti}^{4+}$  ( $\text{IR}=0.605\text{\AA}$  CN=6). Besides, Zhang

report that the complex substitution of  $\text{Al}^{3+}$  and  $\text{Nb}^{5+}$  for  $\text{Ti}^{4+}$  gives rise to a phase transition and then adjust the dielectric performance[14].

Furthermore, along with the developments in LTCC technology, ceramics that could be sintered at low sintering temperature become more and more important[15, 16]. However, most modern commercial materials including LNT have a high processing temperature, which is higher than the melting point of high-electrical-conductivity electrode ( $\text{Ag} \sim 961^\circ\text{C}$ ,  $\text{Cu} \sim 1042^\circ\text{C}$ )[17]. Hence, a lot of attempts to reduce the sintering temperature had been carried out [18, 19]. For example,  $\text{V}_2\text{O}_5$ ,  $\text{B}_2\text{O}_3$  and  $\text{Bi}_2\text{O}_3$  was effectively reduce the sintering temperature of M phase and still maintain excellent performance[20-22]. However, boron trioxide is easily soluble in ethanol, water, and the functional hydroxyl group in PVB would react readily with boron. Besides, vanadium pentoxide is difficult to disperse uniformly in the matrix material, and the viscosity of the slurry containing  $\text{V}_2\text{O}_5$  dielectric material is large. The mentioned problems will make it difficult to obtain a dense cast film strip, and serious quality control problems occur in the manufacture of LTCC[23, 24]. Therefore, suitable sintering aid plays a vital role for the application in LTCC of M phase solid solutions.

Combining with our previous work, LBS glass has large solubility in  $\text{ZnO-Nb}_2\text{O}_5\text{-TiO}_2$  systems[25-27]. Considering the great compatibility with  $\text{Nb}_2\text{O}_5$ -based system, LBS glass was adopted for lowering the temperature sintering. In addition, the effects of LBS on the crystal structure, microstructure, properties and the low temperature mechanism was also discussed.

## 2 Experimental

High purity  $\text{Li}_2\text{CO}_3$ ,  $\text{Nb}_2\text{O}_5$ ,  $\text{TiO}_2$  and  $\text{Al}_2\text{O}_3$  were weighted according to the non-stoichiometric ratio of  $\text{LiNb}_{0.6}\text{Ti}_{(0.5-x)}(\text{Al}_{0.5}\text{Nb}_{0.5})_x\text{O}_3$  (hereafter abbreviated LNT,  $0.06 \leq x \leq 0.14$ ). These compounds were mixed and ball-milled for 5 h with zirconia media in deionized water. These mixtures were calcined at  $870^\circ\text{C}$  for 3 h. The LBS glass was also synthesized via reagent-grade starting materials:  $\text{Li}_2\text{CO}_3$ ,  $\text{H}_3\text{BO}_3$ ,  $\text{SiO}_2$  (40.04:53.72:6.24 wt. %). After milled for 2 h with zirconia ball and deionized water

as milling media. Then the glass melted into a platinum crucible at 1200°C for 2 h. The glass melt was then poured into a copper plate to quench, and vibrated mill for 4 h.

Subsequently, the calcined powders were re-milled for 5 h. Afterwards, 6 wt. % PVA was added to pressed into disks (15 mm in diameter and 8 mm in height) at 20 MPa, and then the samples were sintered at 1100°C for 2 h. With LBS glass added, the calcined LNT powders and LBS were mixed and milled together for 5 h, the mixtures were dried and added with acrylic acid to form pellets, and the specimen were sintered at 850-950°C for 2 h.

The bulk density of the sintered samples was calculated by Archimedes method. X-ray diffraction (Philips X'Pert ProMPD, Amsterdam, The Netherlands) was performed to confirm the phase composition and Cu  $\kappa\alpha$  radiation is provided from the detector. The microstructure of the sample's surface was examined with a scanning electron microscopy (Inspect F). The shrinkage curve of the ceramics was obtained by thermomechanical analyses (TMA) (Model DIL 420C, Netzsch, Germany), with heating rates were 5, 7.5, 10, 12.5, 15 K/min, respectively. Dielectric properties at microwave frequency was obtained by the Hakki-Coleman dielectric resonator method. The measured result was displayed in a network analyzer (Hp83752A, the United States), with the TE<sub>011</sub> mode. Temperature coefficient value was calculated based on the following formula:

$$\tau_f = \frac{f_T - f_{T_0}}{f_{T_0} \times (T - T_0)} \quad (1)$$

Where the  $f_T$  and  $f_{T_0}$  were the TE<sub>011</sub> resonant frequency at temperature T and T<sub>0</sub>, respectively.

### 3 Results

The room temperature XRD patterns of LNT samples sintered at 1100°C for 2 h are plotted in Fig. 1. It can be seen that all patterns can be indexed as Li<sub>1.075</sub>Nb<sub>0.625</sub>Ti<sub>0.45</sub>O<sub>3</sub> phase (JCPDS # 54-1017). In the whole range, no secondary phase could be detected within the resolution limit of the apparatus, which means that

$(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  and  $\text{Ti}^{4+}$  occupied the same position to form a homogeneous solid solution. And the lattice parameters are shown in Table. 1, c-axis decreases linearly only about 0.10%, while a-axis (b-axis) increases about 0.17%, with the increment of doping content. Thus, the unit cell volume is increased inevitably, and the offset of the XRD peak also confirms this, where a similar phenomenon was reported by Mao[28].

Figure 2 shows the SEM images of LNT ceramics with: (a)  $x = 0.06$ , (b)  $x = 0.08$ , (c)  $x = 0.10$ , (d)  $x = 0.12$ , (e)  $x = 0.14$  when sintered at  $1100^{\circ}\text{C}$  for 2 h, and platelet-shaped homogenous microstructures were revealed for all the ceramics. It can be seen that small number of pores can be detected when  $x \leq 0.10$ , while a compact morphology appears at  $x = 0.12$ . It means that as the doping content increases, the microstructure of LNT ceramic specimen becomes densified, which could be confirmed by the bulk density in Fig. 2(f). In addition, as the value of  $x$  increases, the average size of the grains gradually decreases, which is facilitated the formation of densified structure.

The EDS and mapping analysis were utilized to further reveal the microscopic information of LNT ( $x = 0.10$ ), as shown in Fig. 3. Obviously, two kinds of crystal grains namely rod-shaped grains (spot A) and plate-shaped grains (spot B) can be detected in the SEM image of all components shown in Fig. 2. EDS analysis results demonstrated that two type grains have similar elemental proportions, which is consistent with the XRD results. Mapping analysis results shows that all elements except aluminum are distributed in the specimen uniformly. As known to all, the grain boundary energy is the driven force of ceramic sintering, and it can be decreased as a result of the segregation of aluminum at the grain boundaries, which results in a decrease in ion diffusion rate. Several mentioned factors will hinder the movement of the grain boundaries, and thus the growth of crystal grains is suppressed[11], which is consistent with the SEM analysis.

The dielectric characterization as a function of the  $x$  value (at 3.8~4.1 GHz) are plotted in Fig 4. Although the polarizability of  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  ( $2.38 \text{ \AA}$ ) is smaller than that of  $\text{Ti}^{4+}$  ( $2.93 \text{ \AA}$ )[29], the  $\epsilon_r$  of LNT ceramics increased linearly from 67 to 72 while the doping amount increased from 0.06 to 0.14, owing to the improvement of

densification. The dielectric constant of the pores in the microwave frequency band is about 1, which is much lower than the dielectric constant of the LNT phase, therefore, the existence of pores affects the  $\varepsilon_r$  seriously[30]. Thus, the  $\varepsilon_r$  value monotonously increases along with the improvement of bulk density. It is well accepted that the Q value of microwave dielectric ceramics is affected by complex factors including intrinsic loss and extrinsic loss. Intrinsic loss is associated with the absorptions of phonon oscillation, extrinsic loss is related to lattice defect, such as impurity, cavity, substitution, grain boundaries, size and second phases, pores, etc[31-34]. From the SEM image, as the doping amount increases, although the improvement of densification will benefit  $Q \times f$ , the effect of small grains will generate more grain boundaries, which will lead to a drop of  $Q \times f$  value[35].

The  $\tau_f$  value is a key factor for microwave dielectric ceramics. It determines the temperature stability of dielectric ceramics. As is shown in Fig 4, the  $\tau_f$  of LNT decreased from 24.2 to -14.8 ppm/°C with the increment of doping content. This implies that the substitution of  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  for  $\text{Ti}^{4+}$  effectively improves  $\tau_f$  values. As known,  $\tau_f$  and the permittivity temperature coefficient  $\tau_\varepsilon$  are presented in Equation 1:

$$\tau_f = -(\alpha_l + \frac{1}{2}\tau_\varepsilon) \quad (1)$$

where  $\alpha_l$  represent the linear thermal expansion coefficient. The influence of  $\alpha_l$  on  $\tau_f$  can be ignored since  $\alpha_l$  is always in the range of 10ppm/°C. Therefore,  $\tau_f$  values is mainly determined by  $\tau_\varepsilon$ , which is deduced by the following formula:

$$\tau_\varepsilon = \frac{1}{\varepsilon} \left( \frac{\partial \varepsilon}{\partial T} \right) = \frac{(\varepsilon - 1)(\varepsilon + 2)}{3\varepsilon} \times (A + B + C) \quad (2)$$

$$A = -\frac{1}{V} \left( \frac{\partial V}{\partial T} \right)_P \quad (3)$$

$$B = \frac{1}{\alpha_D} \left( \frac{\partial \alpha_D}{\partial V} \right)_T \times \left( \frac{\partial V}{\partial T} \right)_P \quad (4)$$

$$C = \frac{1}{\alpha_D} \left( \frac{\partial \alpha_D}{\partial T} \right)_V \quad (5)$$

where  $\alpha_D$  is the ionic polarizability. According to the theory of Bosman et al.<sup>[36]</sup>, generally, the sum of the A and B terms is approximately  $6 \pm 1 \text{ ppm/}^\circ\text{C}$ . And C is in the range of -1 to -10  $\text{ppm/}^\circ\text{C}$ . Since the range of change of C is bigger than the sum of A and B, it is expected that  $\tau_e$  will largely depend on C. Lee<sup>[37]</sup> believes that the C is related to the crystal structure and cell parameters. And according to Yoon et al.<sup>[38]</sup>, the unit cell volume has a strongly positive correlation with the lattice energy, subsequently,  $\tau_e$  should be proportional to the cell volume. Corresponding to the lattice parameter shown in Table 1, the unit cell volume increases with the increase of  $x$ , so the  $\tau_e$  keeps increasing, as a result, the resonant frequency temperature coefficient  $\tau_f$  decrease as the  $(\text{Al}_{0.5}\text{Nb}_{0.5})^{4+}$  incorporation increases.

The LNT ceramics sintered at  $1100^\circ\text{C}$  shows excellent microwave properties. However, the sintering temperature is not suitable for the requirement in LTCC. Thus, glass frit with a chemical composition of  $\text{Li}_2\text{O}-\text{B}_2\text{O}_3-\text{SiO}_2$  (LBS) was chosen to lower the sintering temperature of the component with the best temperature stability as  $x = 0.10$ , and the amount of LBS was selected as 0.5~2.0 wt. %.

The XRD patterns of LNT ceramics sintered at their optimal temperature with different content of LBS (Fig 5(a)) and different temperature with 1.0 % LBS (Fig 5(b)) are exhibited. All diffraction peaks can be indexed to  $\text{Li}_{1.075}\text{Nb}_{0.625}\text{Ti}_{0.45}\text{O}_3$  (JCPDS # 54-1017). No second phase appeared, indicating that a single phase of LNT was obtained at low sintering temperature.

The SEM images of the as-fired surfaces of LNT samples sintered at  $925^\circ\text{C}$  with different amount of LBS are shown in Fig.6 (a)-(d), the corresponding EDS analysis of 1.0 wt. % LBS was also provided. The EDS results revealed that the bright white area is the LNT grain and the gray area is the glass phase. All samples exhibit a uniform grain size and liquid phase appears. More fused glass was observed as the additive content increases, which is benefit for packing the ceramics to improve the densification. However, when the sintering aid exceeds an appropriate content (1.0 wt. %), the glass phase would deteriorate the performance of the specimen because of the poor performance of LBS ( $\epsilon_r = 7.58$ ,  $\tan\delta(\%) = 0.45$ ,  $\tau_f = -86 \text{ ppm/}^\circ\text{C}$ )[27].

The variations of  $\epsilon_r$  value and bulk density of each composition sintered at



various temperature are plotted in Fig.7. As shown, the curves for different content of glass doped samples are analogous. The density of each samples increases with the increase of sintering temperature and then remains saturated. The densities of the specimens doped with 0.5 wt. % LBS sintered at 850°C remain relatively low while the LBS glass content increased to above 1.0 wt. %, the samples could reach high densities ( $4.11\text{g/cm}^3$ ) at around 925°C. Besides, XRD results shown that no second phase formed during sintering, and the dielectric polarizability of LNT remains unchanged, the density and the additives should be a key factor for the change in  $\epsilon_r$  value. The variations of  $\epsilon_r$  value represents an analogous trend with the bulk density. Only when the sintering temperature and the number of additives are appropriate, the  $\epsilon_r$  can reach the optimum value.

The fluctuation of  $Q \times f$  value at different sintering conditions are plotted in Fig 8(a). Generally speaking, the change of  $Q \times f$  and bulk density are consistent. The insufficient performance of the ceramics with 0.5wt. % glass sintered at 850 °C arises from the poor densification. After increasing the sintering temperature, the  $Q \times f$  value increased sharply. A relatively good performance has been obtained when the content of the glass is 1.0 wt. % because of a high densification, which can be confirmed in Fig 8(a). It is worthy to note that when the glass content is high ( $\geq 1.5\text{wt. \%}$ ), a negative influence on the  $Q \times f$  value shows due to the formation of a large amount of liquid phase.

Figure 8(b) shows the  $\tau_f$  and  $\epsilon_r$  of LNT with 1.0 wt. % LBS. Since LBS glass has a negative  $\tau_f$  values of  $-86\text{ ppm/}^\circ\text{C}$  [27], the  $\tau_f$  value of the system decrease after the addition of glass. And the  $\tau_f$  value increases towards to zero with the increase of sintering temperature shows a similar trend to the  $\epsilon_r$ . The microwave dielectric properties of typically high  $\epsilon_r$  LTCC materials are summarized in Tab 2 [3, 27, 39-43].

For further investigate the sintering mechanism of LNT with LBS, the shrinkage curves of LNT samples added with 1.0 wt. % LBS under a sintering rate between 5-15 K/min are shown in Fig. 9. The samples un-doped glass starts to shrink at about 850°C and shrinkage reaches to maximum(15.2%) when the temperature reaches 1150°C. After adding a small content of LBS (1.0 wt. %), the samples begin to shrink at 650°C.

For better exploring liquid phase sintering mechanism, the activation energies ( $E_a$ ) which represents the minimum energy to meet the ceramic densification requirements during sintering of LNT ceramic un-doped and doped LBS were calculated according following equation:

$$\ln k = -\frac{E_a}{R} \left( \frac{1}{T} \right) + \ln z$$

where  $R=8.3145$  J/K/mol,  $k$  is the heating rate of 5 K/min, 7.5 K/min, 10 K/min, 12.5 K/min, 15 K/min,  $T$  represents the Kelvin temperature(K),  $z$  is a constant value.

In addition, the relationship of  $1/T$  versus  $1000 \ln k$  plots in Fig 10. The fitted results indicate an average  $E_a$  value of  $455.91 \pm 68.00$  kJ/mol for un-doped LBS glass and an average  $E_a$  of  $295.11 \pm 77.45$  kJ/mol for LNT doped 1.0 wt. % LBS. The decline of  $E_a$  also confirm the presence of low-temperature liquid phase produced by LBS glass directly accelerate the low temperature sintering process.

#### 4 Conclusion:

In this work, the  $(Al_{0.5}Nb_{0.5})^{4+}$  ionic co-substitutions for  $Ti^{4+}$  of  $LiNb_{0.6}Ti_{0.5}O_3$  ( $0.06 \leq x \leq 0.14$ ) ceramics was investigated. The XRD patterns and EDS analysis result indicated a formation of  $Li_{1.075}Nb_{0.625}Ti_{0.45}O_3$  solid solution without secondary phases. The SEM photograph shows that as the amount of doping increases, an increasingly densified microstructure appears, which bring in the increase of  $\epsilon_r$  value. Besides, the small size of grain inevitably leads to an increase of grain boundaries, which have a negative influence on  $Q \times f$  value. The  $\tau_f$  values could be continuously shifted to near zero. Excellent microwave dielectric properties were obtained in LNT ceramics ( $x = 0.10$ ) when sintered at  $1100^\circ\text{C}$  for 2 h:  $\epsilon_r = 70.34$ ,  $Q \times f = 5144$  GHz (at 3.85 GHz),  $\tau_f = 4.8\text{ppm}/^\circ\text{C}$ . For explore the practical use of LNT ceramics in LTCC field, the responsibility of LBS glass for lowering the sintering temperature, and the relevance of various LBS content to the sintering behavior, activation energy, phase composition, and microwave dielectric properties were also collected in this work. Indeed, LBS glass can reduce the activation energy required for the reaction sintering process, subsequently reducing the sintering temperature from  $1100^\circ\text{C}$  to  $925^\circ\text{C}$ . Satisfied

balance of microwave dielectric properties for  $x = 0.10$  were obtained with 1.0 wt. % glass at 925°C for 2 h:  $\epsilon_r = 70.16$ ,  $Q \times f = 4153$  GHz,  $\tau_f = -0.65$  ppm/°C.

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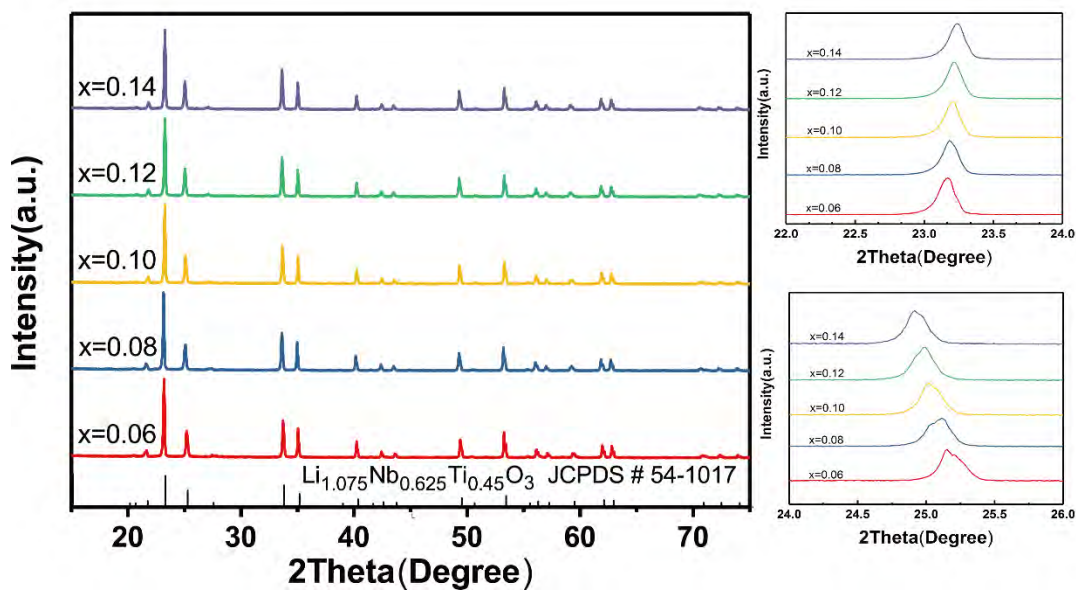


Figure 1. The XRD patterns of LNT ceramics sintered at 1100°C for 2 h

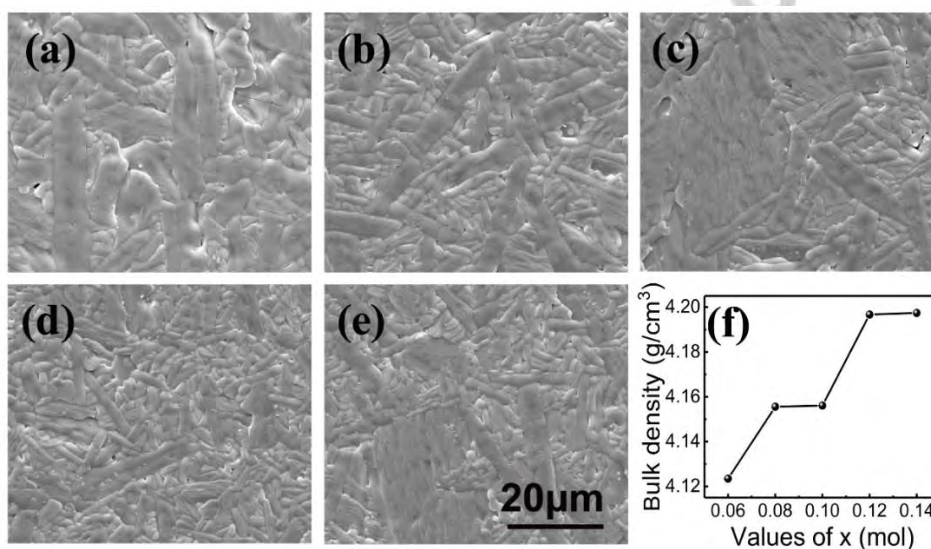


Figure 2. The SEM photograph of LNT ceramics with: (a)  $x = 0.06$ , (b)  $x = 0.08$ , (c)  $x = 0.10$ , (d)  $x = 0.12$ , (e)  $x = 0.14$  when sintered at 1100°C for 2 h and (f) bulk density of ceramics

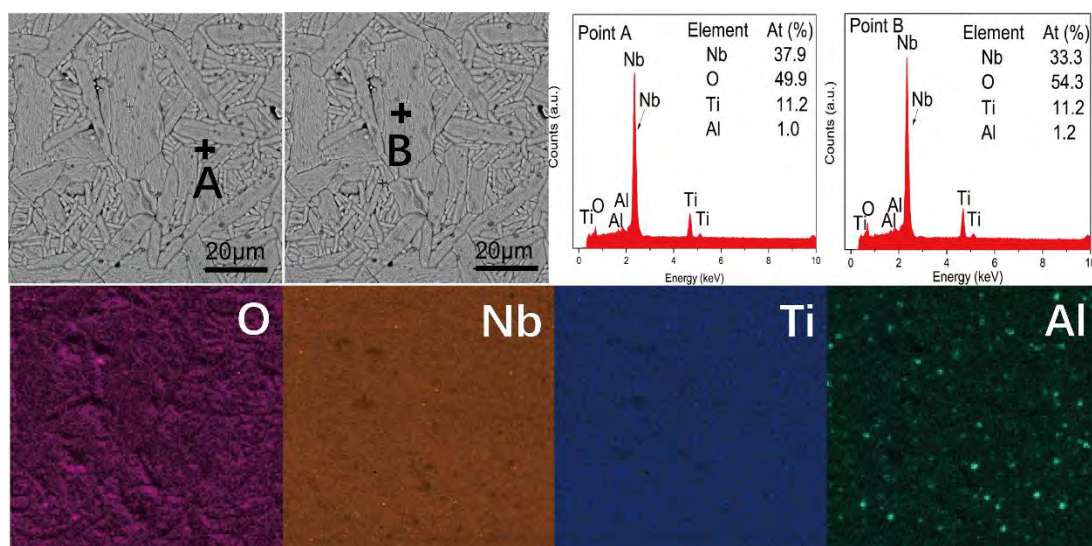


Figure 3. The EDS analysis of spot A and B of LNT ceramic ( $x = 0.10$ ) and Element mapping of the LNT ceramic ( $x = 0.10$ )

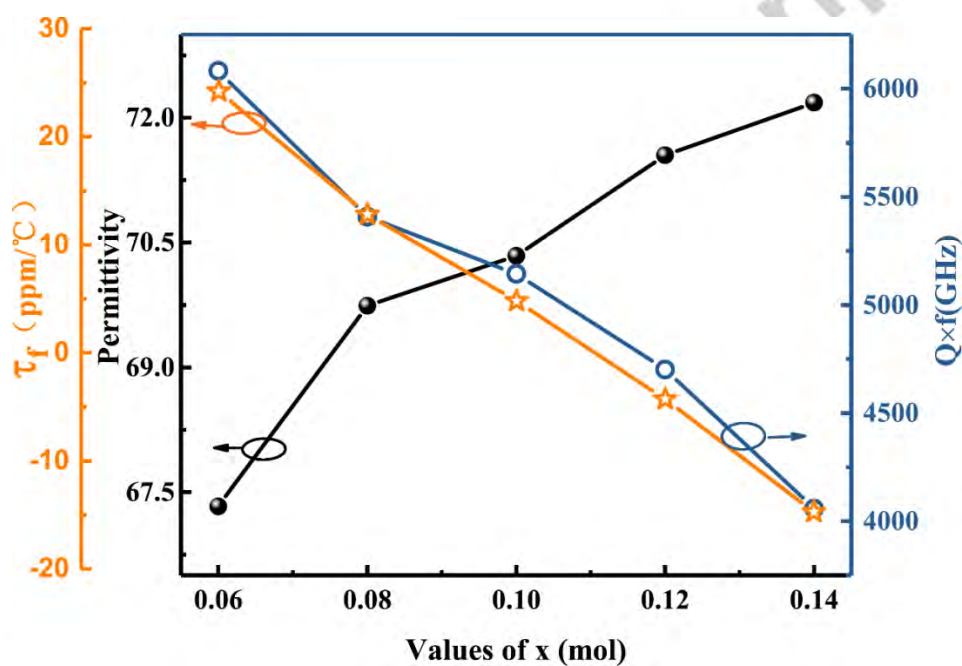


Figure 4. The microwave dielectric properties of LNT ceramic



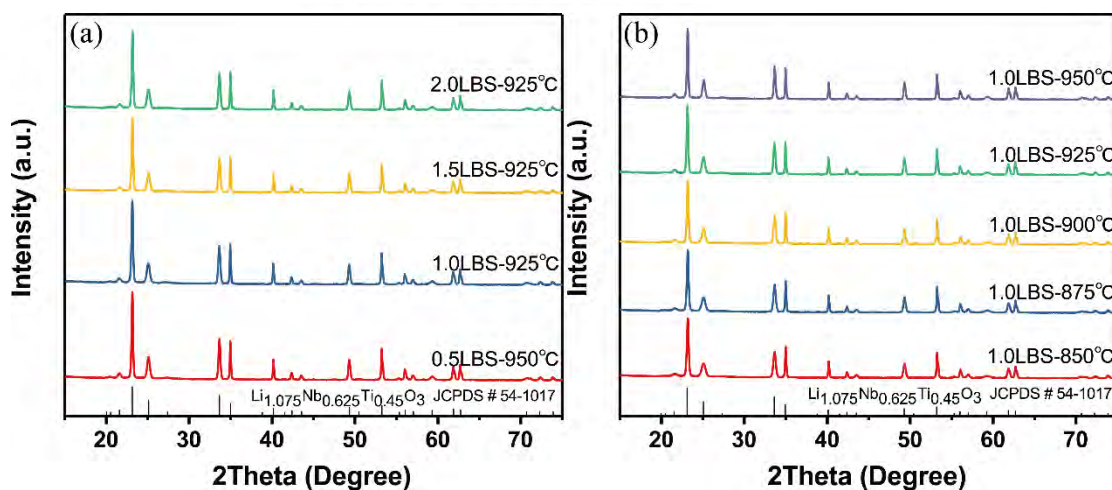


Figure 5. (a) The XRD patterns of the ceramics at optimum sintering temperature for 2 h with different content of LBS glass; (b) The XRD patterns of the ceramics sintered at 850~950 °C with 1.0 wt. % LBS glass.

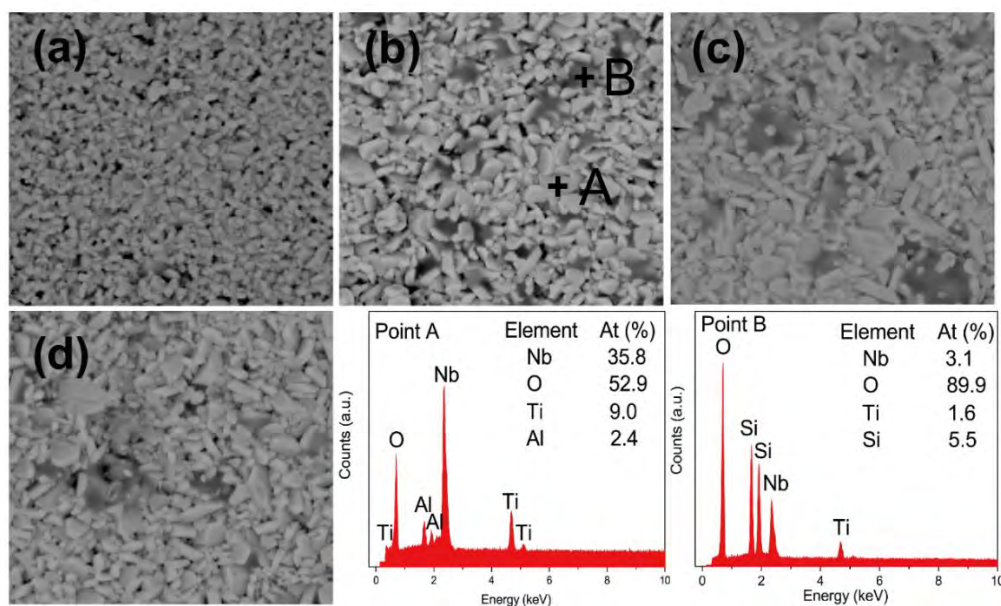


Figure 6. The SEM images of LNT ceramic with different amount of LBS glass sintered at 925°C (a) 0.5 wt. %, (b) 1.0 wt. %, (c) 1.5 wt. %, (d) 2.0 wt. % and EDS analysis of LNT ceramic (with 1.0 wt. % LBS)



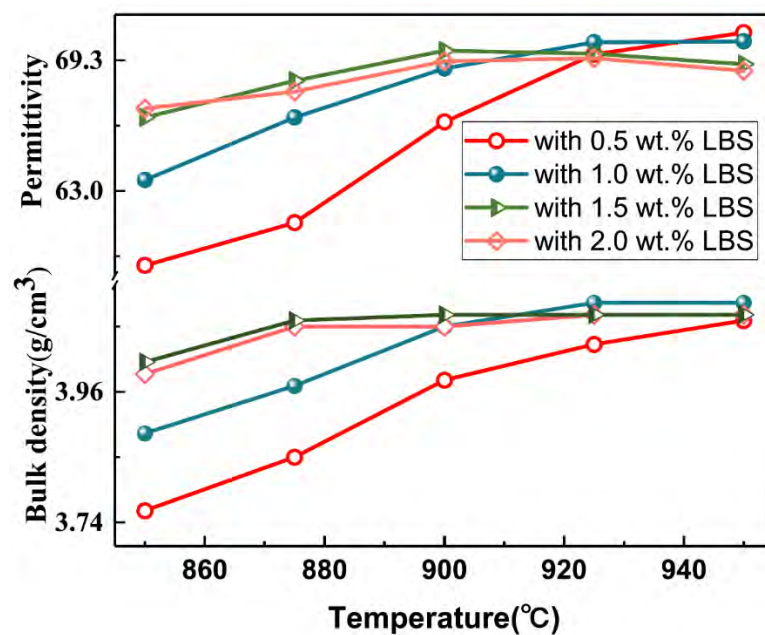


Figure 7. The  $\epsilon_r$  value and bulk density of the LNT ceramics with different LBS addition versus sintering temperature

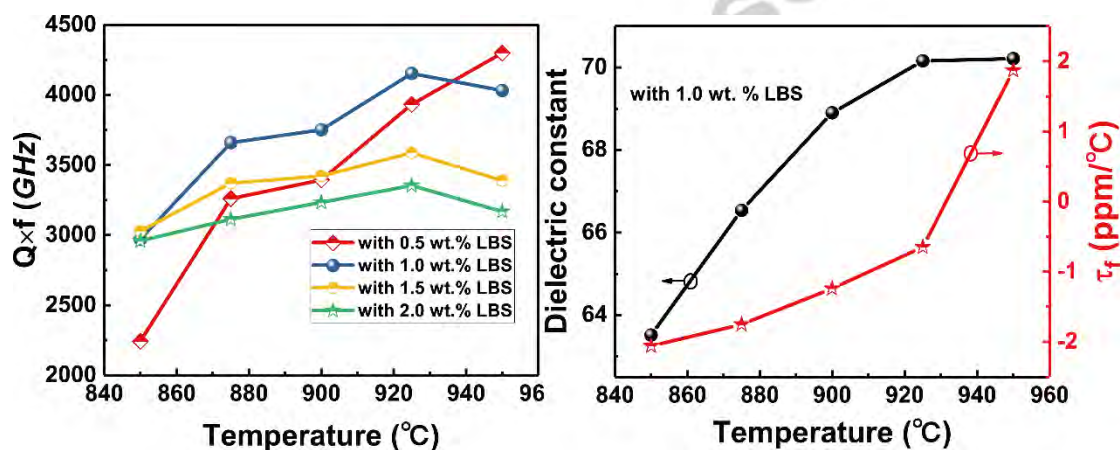


Figure 8. The microwave dielectric properties of the LNT ceramics with different LBS addition versus sintering temperature

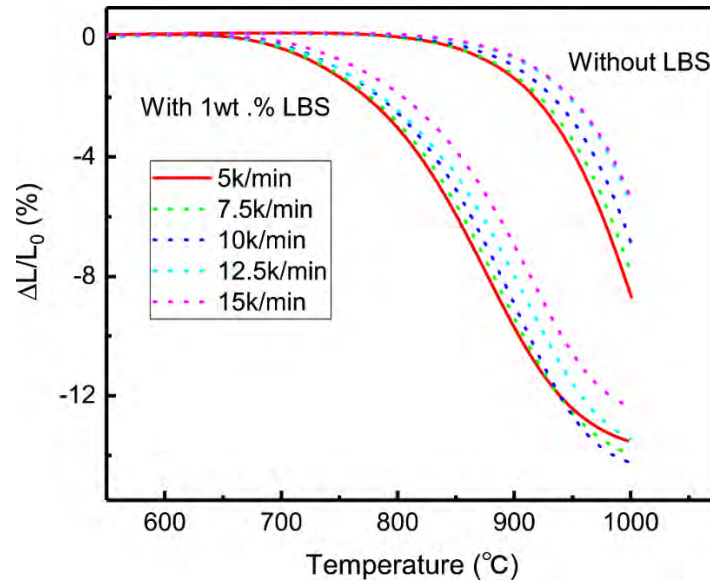


Figure .9 The shrinkage curve of LNT samples undoped and doped with 1.0 wt. % LBS addition.

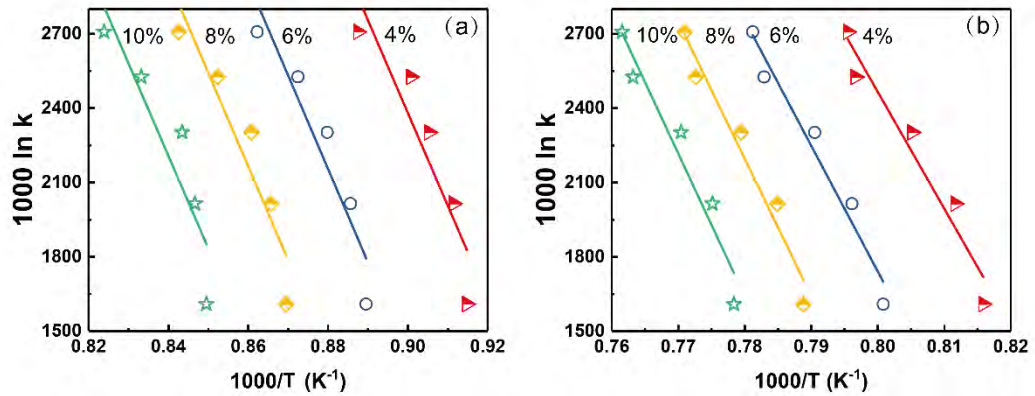


Figure 10. The  $1000 \ln k$  as a function of  $1/T$  at different shrinkage, where (a): without LBS, (b) with 1.0 wt. %LBS

Table 1. The lattice parameter of LNT ceramics

$x$	Cell parameters				$V_{\text{unit}} (\text{\AA}^3)$
	$a=b(\text{\AA})$	$c(\text{\AA})$	$\alpha=\beta (^{\circ})$	$\gamma (^{\circ})$	
0.06	5.11997	13.91466	90	120	315.89
0.08	5.12382	13.90891	90	120	316.24
0.10	5.12567	13.90377	90	120	316.35
0.12	5.12735	13.90351	90	120	316.55
0.14	5.12879	13.90007	90	120	316.65

Table 2. The microwave dielectric properties of typically high  $\epsilon_r$  LTCC

Chemical composition	ST (°C)	$\epsilon_r$	$Q \times f$ (GHz)	$\tau_f$ (ppm/°C)	Ref.
0.02BFM -0.98BV	820	72.9±0.2	13500±300	-270	39
0.10BFM -0.90BV	820	74.8±0.2	11600±300	+170	39
0.02BFM -0.98BV+0.10BFM -0.90BV	820	74.8±0.2	13000±300	+20	39
BNT+3.0 wt.%LBS+3.0 wt.% BZB	900	69.78	4416	46.05	40
Zn <sub>0.15</sub> Nb <sub>0.3</sub> Ti <sub>0.55</sub> O <sub>2</sub> +1.5 wt.% LBS	900	73.59	8024	270.54	27
0.08Bi <sub>2</sub> Ti <sub>4</sub> O <sub>11</sub> +2.0 wt.% CuO	900	81	3500	-5.1	41
0.45BV–0.55TiO <sub>2</sub>	900	86	9500	-8	42
CLT+3.0 wt.% LBZ+1.0 wt.% VC	900	98.94	4885	305.17	43
Bi <sub>2</sub> (Li <sub>0.5</sub> Ta <sub>1.5</sub> )O <sub>7</sub> +2.0 mol.% Bi <sub>2</sub> O <sub>3</sub>	920	64.1	11200	-19	3
This Work	925	70.16	4153	-0.65	

BFM: Bi(Fe<sub>1/3</sub>Mo<sub>2/3</sub>)O<sub>4</sub>; BV: BiVO<sub>4</sub>; BNT: BaNd<sub>2</sub>Ti<sub>4</sub>O<sub>12</sub>; CLT:Ca<sub>0.6</sub>La<sub>0.268</sub>TiO<sub>3</sub>